

FEATURES

- Low Switching Losses At High Frequency.
- Fully Characterised For Operation Up To 20kHz.

APPLICATIONS

- High Power Inverters And Choppers.
- UPS.
- AC Motor Drives.
- Induction Heating.
- Cycloconverters.

VOLTAGE RATINGS

Type Number	Repetitive Peak Voltages V_{DRM} V_{RRM}	Conditions
DK13 08FW K or M DK13 06FW K or M	800 600	$V_{RSM} = V_{RRM} + 100V$ $I_{DRM} = I_{RRM} = 15mA$ at V_{RRM} or V_{DRM} & T_{vj}

ORDERING INFORMATION

When ordering, select the required part number shown in the Voltage Ratings selection table, then:-

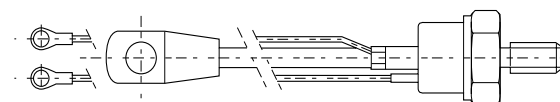
Add K to type number for 1/2" 20 UNF thread, e.g. **DK13 06FWK**
or

Add M to type number for M12 thread, e.g. **DK13 06FM**.

Note: Please use the complete part number when ordering and quote this number in any future correspondence relating to your order.

KEY PARAMETERS

V_{DRM}	800V
$I_{T(RMS)}$	110A
I_{TSM}	1200A
dV/dt	200V/μs
dI/dt	200A/μs
t_q	10μs



Outline type code: TO94
See Package Details for further information.

Fig. 1 Package outline

CURRENT RATINGS

Symbol	Parameter	Conditions	Max.	Units
$I_{T(AV)}$	Mean on-state current	Half wave resistive load, $T_{case} = 80^{\circ}C$	70	A
$I_{T(RMS)}$	RMS value	$T_{case} = 80^{\circ}C$	110	A

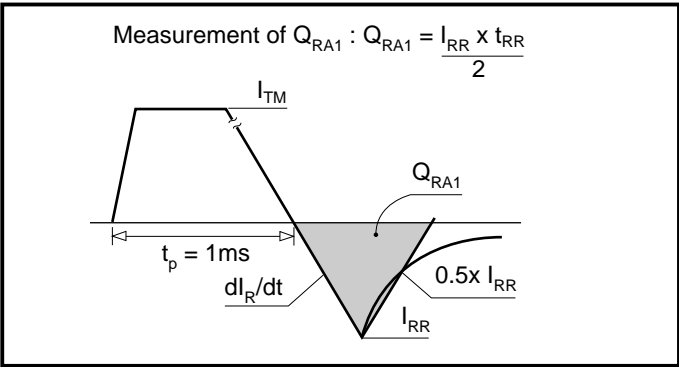
SURGE RATINGS

Symbol	Parameter	Conditions	Max.	Units
I_{TSM}	Surge (non-repetitive) on-state current	$t_p = 10ms$ half sine; $T_{case} = 125^{\circ}C$	1.2	kA
I^2t	I^2t for fusing	$V_R = 0\% V_{RRM} - 1/4$ sine	7.2×10^3	A ² s

THERMAL AND MECHANICAL DATA

Symbol	Parameter	Conditions	Min.	Max.	Units
$R_{th(j-c)}$	Thermal resistance - junction to case	dc	-	0.24	$^{\circ}C/W$
$R_{th(c-h)}$	Thermal resistance - case to heatsink	Mounting torque 15.0Nm with mounting compound	-	0.08	$^{\circ}C/W$
T_{vj}	Virtual junction temperature	On-state (conducting)	-	125	$^{\circ}C$
		Reverse (blocking)	-	125	$^{\circ}C$
T_{stg}	Storage temperature range		-40	150	$^{\circ}C$
-	Mounting torque		12.0	15.0	Nm

MEASUREMENT OF RECOVERED CHARGE - Q_{RA1}



DYNAMIC CHARACTERISTICS

Symbol	Parameter	Conditions		Min.	Max.	Units	
V _{TM}	Maximum on-state voltage	At 300A peak, T _{case} = 25°C		-	2.35	V	
I _{RRM} /I _{DRM}	Peak reverse and off-state current	At V _{RRM} /V _{DRM} , T _{case} = 125°C		-	15	mA	
dV/dt	Maximum linear rate of rise of off-state voltage	Linear to 60% V _{DRM} T _j = 125°C, Gate open circuit		-	200	V/μs	
dI/dt	Rate of rise of on-state current	Gate source 20V, 20Ω	Repetitive 50Hz	-	500	A/μs	
		t _r < 0.5μs, T _j = 125°C	Non-repetitive	-	800	A/μs	
V _{T(TO)}	Threshold voltage	At T _{vj} = 125°C		-	1.65	V	
r _T	On-state slope resistance	At T _{vj} = 125°C		-	3.5	mΩ	
t _{gd}	Delay time	T _j = 25°C, I _T = 50A, V _D = 300V, I _G = 1A, dI/dt = 50A/μs, dI _G /dt = 1A/μs		-	3	μs	
t _{(ON)TOT}	Total turn-on time			-	1.5	μs	
I _H	Holding current	T _j = 25°C, I _{TM} = 1A, V _D = 12V		60*	-	mA	
t _q	Turn-off time	T _j = 125°C, I _T = 100A, V _R = 50V, dV/dt = 200V/μs (Linear to 60% V _{DRM}), dI _R /dt = 30A/μs, Gate open circuit		t _q code: W	-	10	μs

*Typical value.

GATE TRIGGER CHARACTERISTICS AND RATINGS

Symbol	Parameter	Conditions	Typ.	Max.	Units
V_{GT}	Gate trigger voltage	$V_{DRM} = 12V$, $T_{case} = 25^{\circ}C$, $R_L = 6\Omega$	-	3.0	V
I_{GT}	Gate trigger current	$V_{DRM} = 12V$, $T_{case} = 25^{\circ}C$, $R_L = 6\Omega$	-	200	mA
V_{GD}	Gate non-trigger voltage	At V_{DRM} , $T_{case} = 125^{\circ}C$, $R_L = 1k\Omega$	-	0.2	V
V_{RGM}	Peak reverse gate voltage		-	5.0	V
I_{FGM}	Peak forward gate current	Anode positive with respect to cathode	-	4	A
P_{GM}	Peak gate power		-	16	W
$P_{G(AV)}$	Mean gate power		-	3.0	W

CURVES

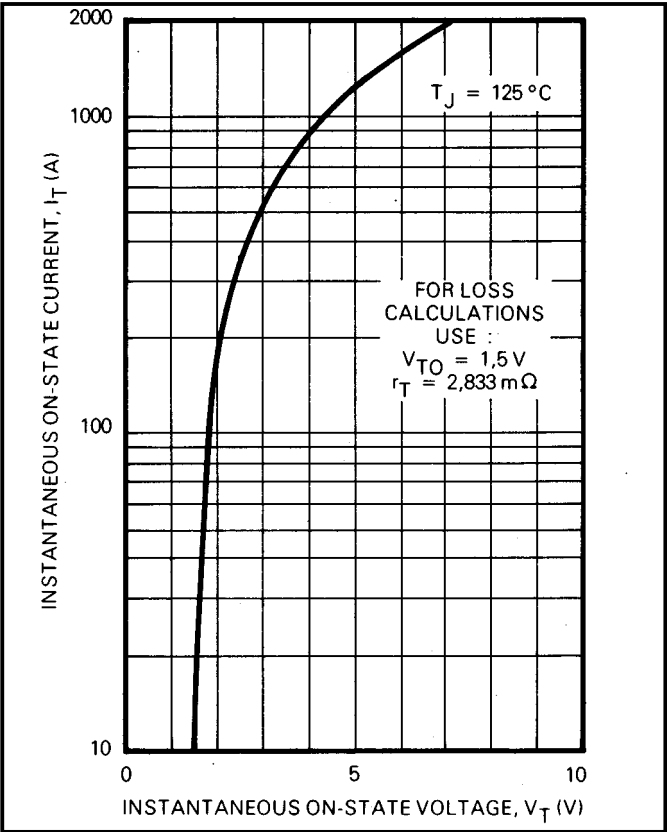


Fig.2 Maximum (limit) on-state characteristics

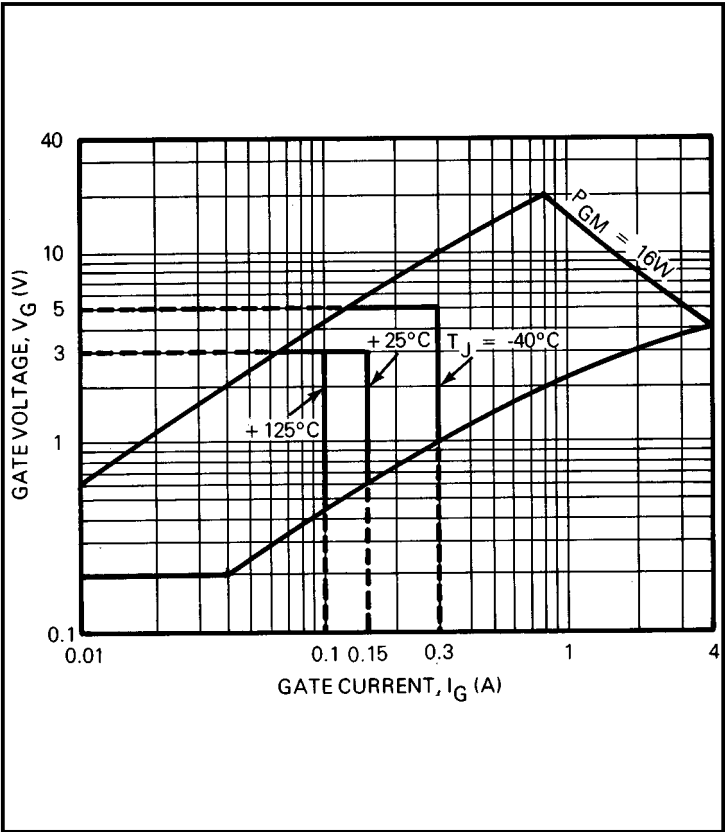


Fig.3 Gate characteristics

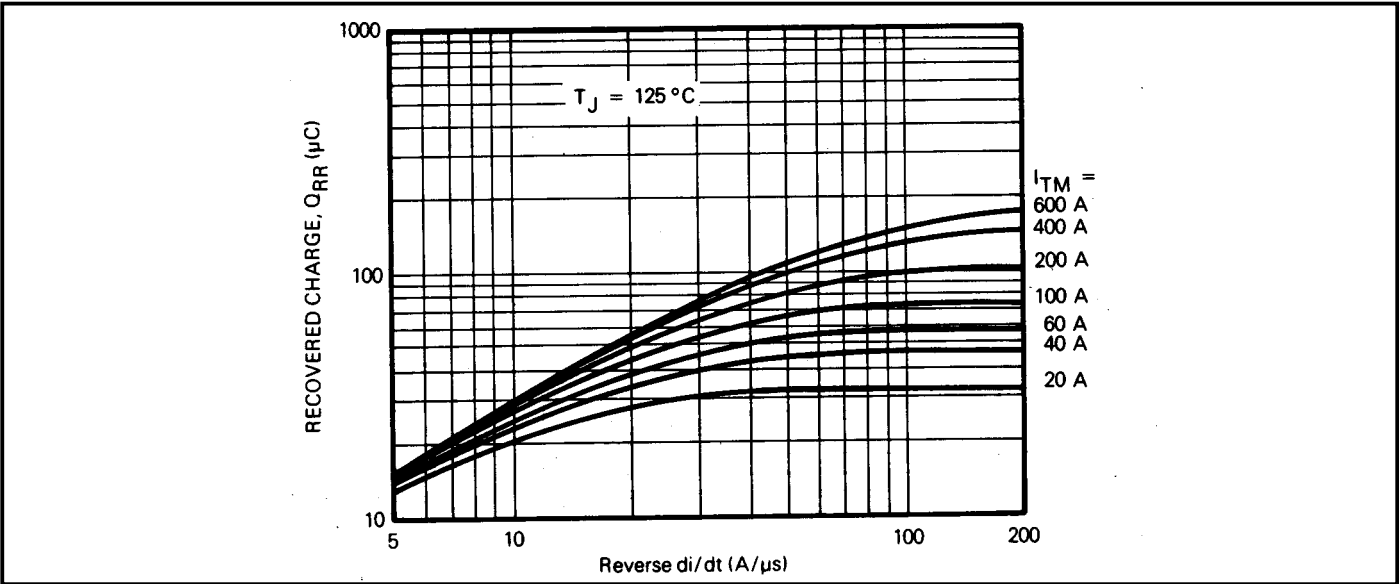


Fig.4 Typical recovered charge (for a device rated $V_{DRM} = 600\text{ V}$, $t_q = 10\mu\text{s}$)

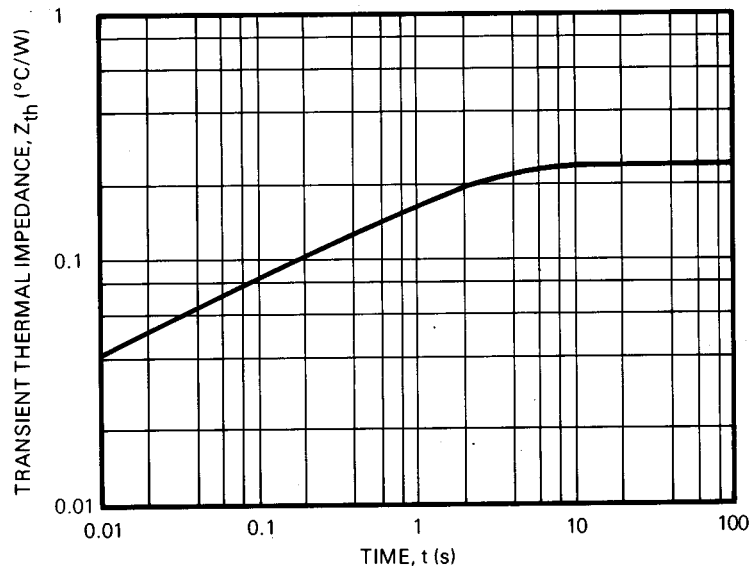


Fig.5 Transient thermal impedance - junction to case

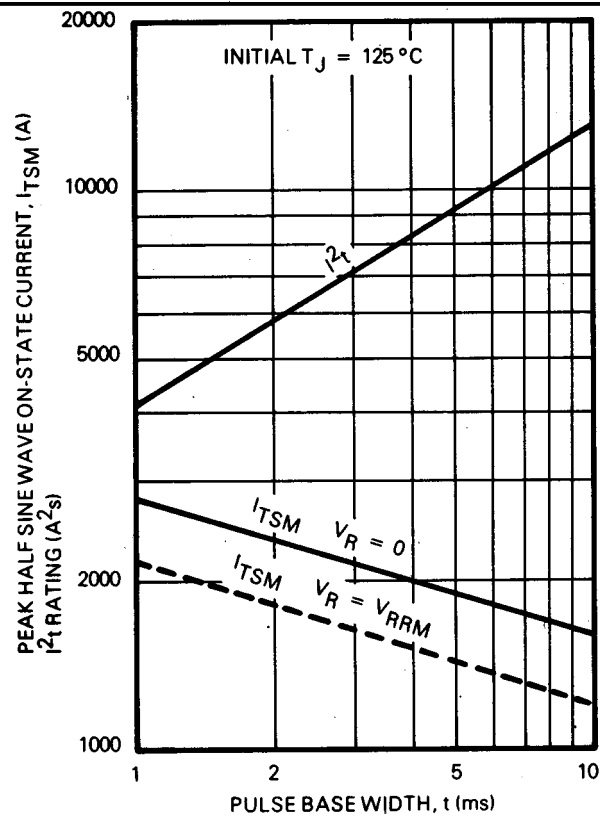


Fig.6 Non-repetitive sub-cycle surge on-state current and I^2t rating

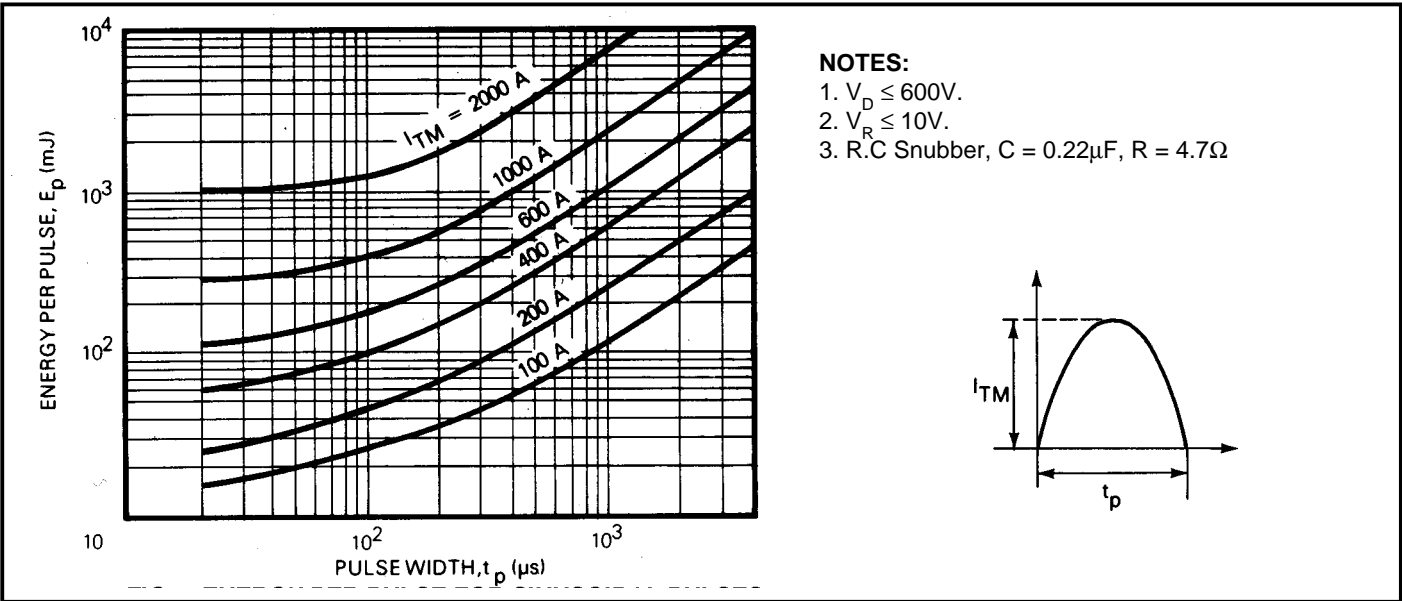


Fig.7 Energy per pulse for sinusoidal pulses

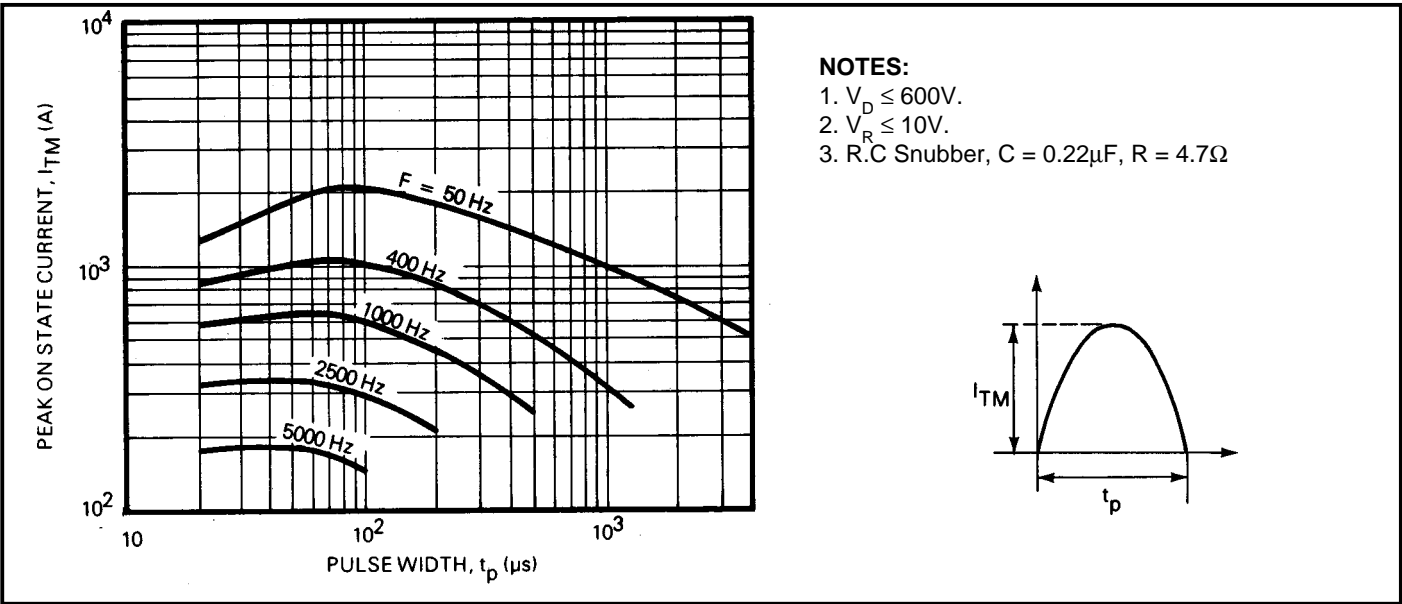
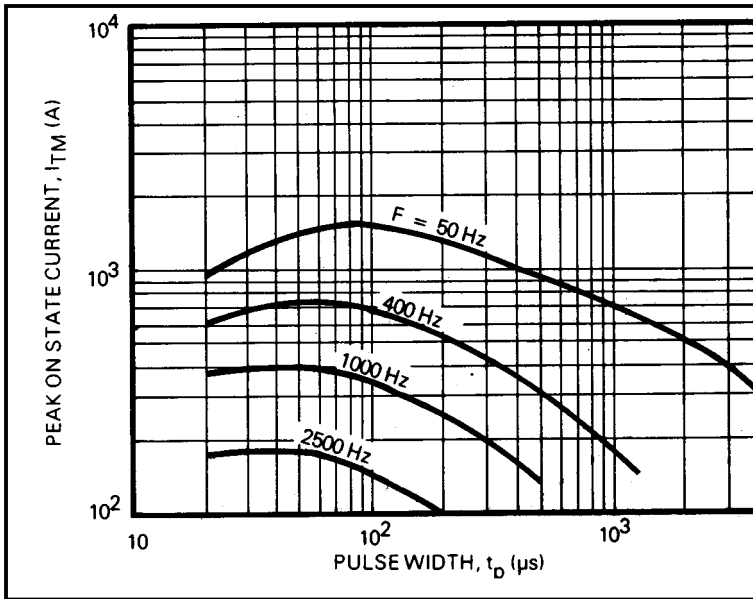


Fig.8 Maximum allowable peak on-state current vs pulse width for $T_{case} = 65^\circ C$



NOTES:

1. $V_D \leq 600V$.
2. $V_R \leq 10V$.
3. R.C Snubber, $C = 0.22\mu F$, $R = 4.7\Omega$

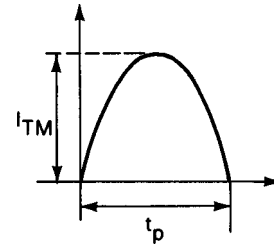
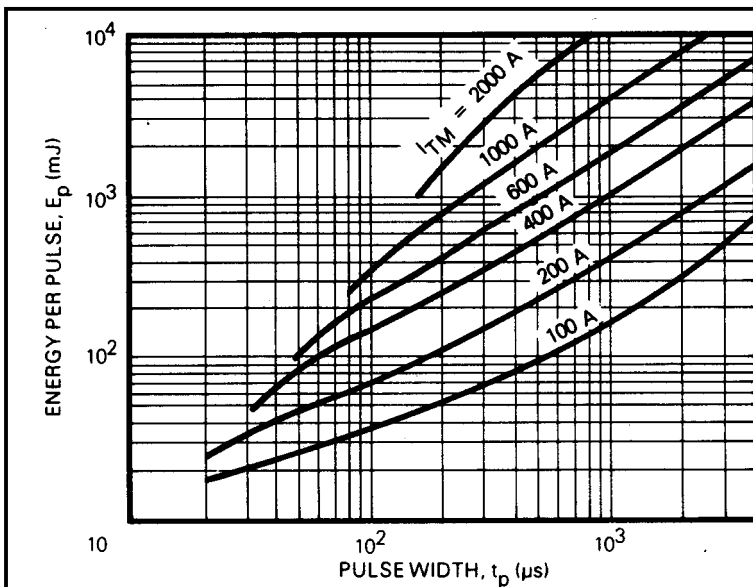


Fig.9 Maximum allowable peak on-state current vs pulse width for $T_{case} = 90^\circ C$



NOTES:

1. $di/dt = 25A/\mu s$
2. $V_D \leq 600V$.
3. $V_R \leq 10V$.
4. R.C Snubber, $C = 0.22\mu F$, $R = 4.7\Omega$

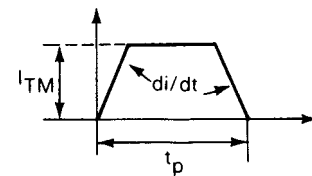
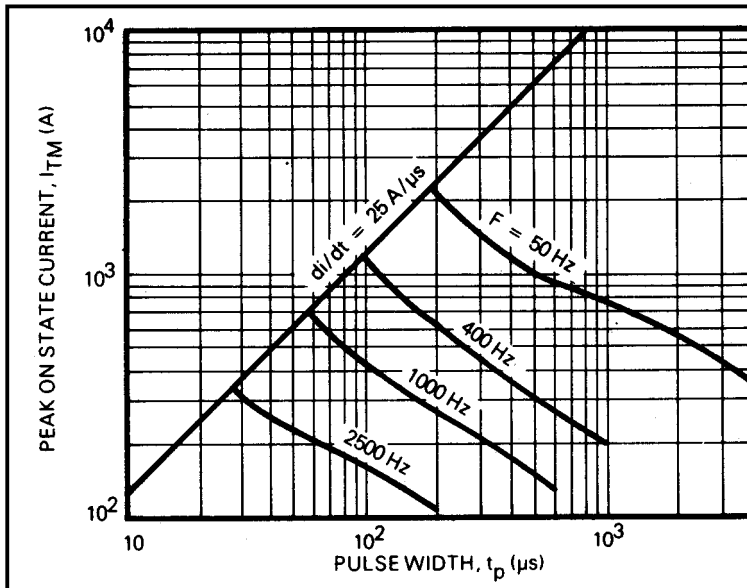


Fig.10 Energy per pulse for trapezoidal pulses

**NOTES:**

1. $di/dt = 25 A/\mu s$
2. $V_D \leq 600V$.
3. $V_R \leq 10V$.
4. R.C Snubber, $C = 0.22\mu F$, $R = 4.7\Omega$

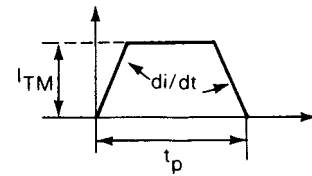
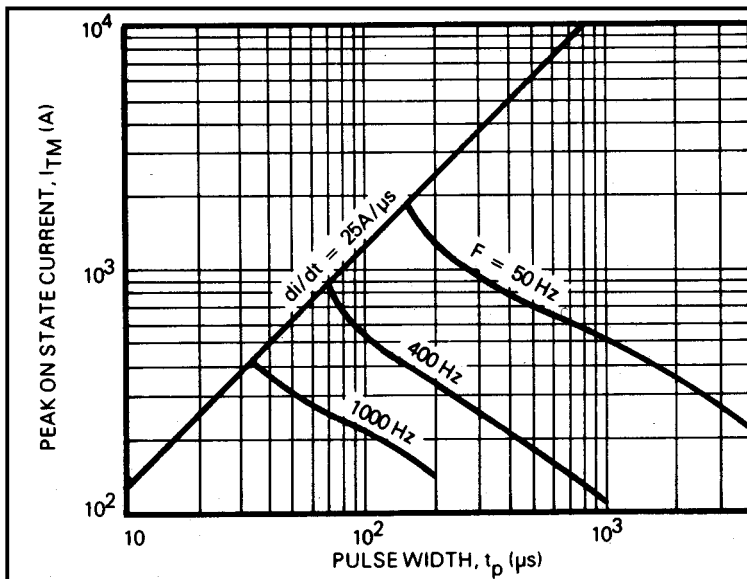


Fig.11 Maximum allowable peak on-state current vs pulse width for $T_{case} = 65^\circ C$

**NOTES:**

1. $di/dt = 25 A/\mu s$
2. $V_D \leq 600V$.
3. $V_R \leq 10V$.
4. R.C Snubber, $C = 0.22\mu F$, $R = 4.7\Omega$

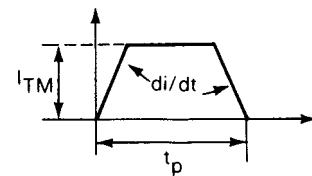
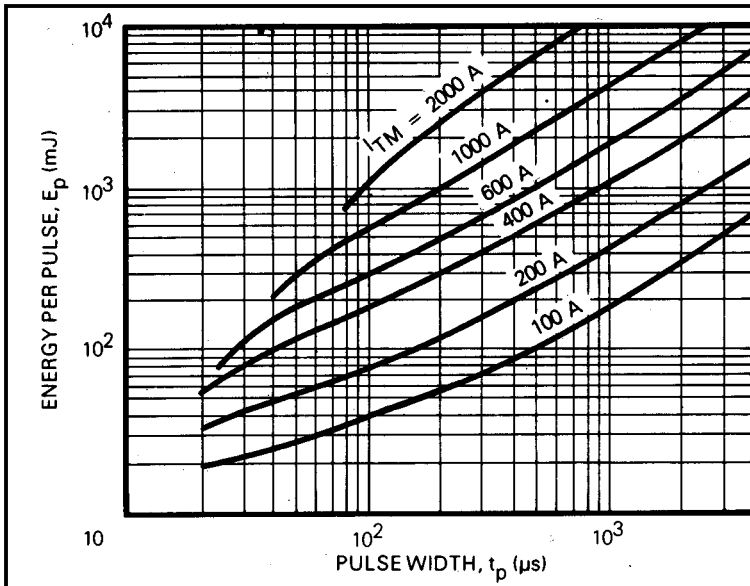


Fig.12 Maximum allowable peak on-state current vs pulse width for $T_{case} = 90^\circ C$



NOTES:

1. $di/dt = 50 \text{ A}/\mu\text{s}$
2. $V_D \leq 600 \text{ V}$.
3. $V_R \leq 10 \text{ V}$.
4. R.C Snubber, $C = 0.22 \mu\text{F}$, $R = 4.7 \Omega$

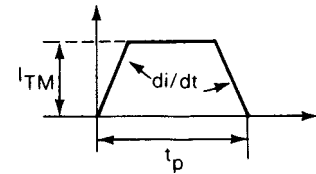
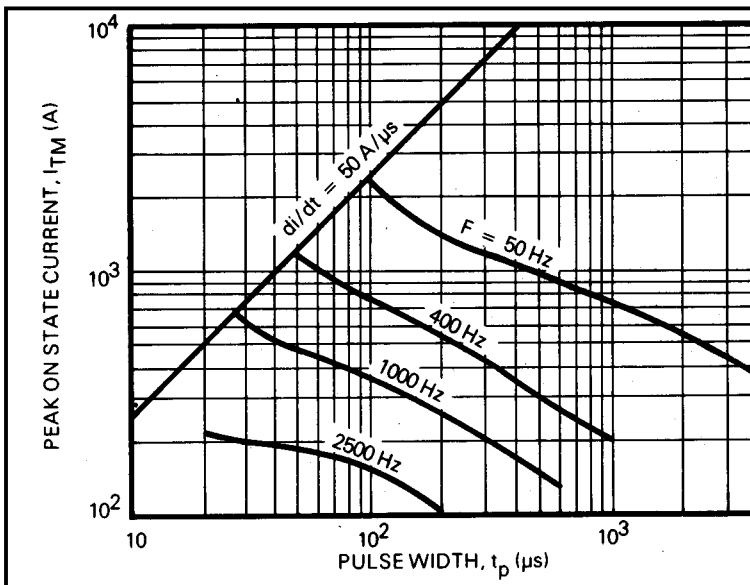


Fig.13 Energy per pulse for trapezoidal pulses



NOTES:

1. $di/dt = 50 \text{ A}/\mu\text{s}$
2. $V_D \leq 600 \text{ V}$.
3. $V_R \leq 10 \text{ V}$.
4. R.C Snubber, $C = 0.22 \mu\text{F}$, $R = 4.7 \Omega$

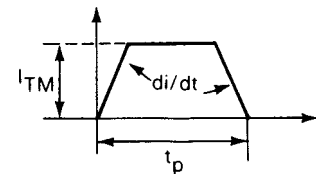
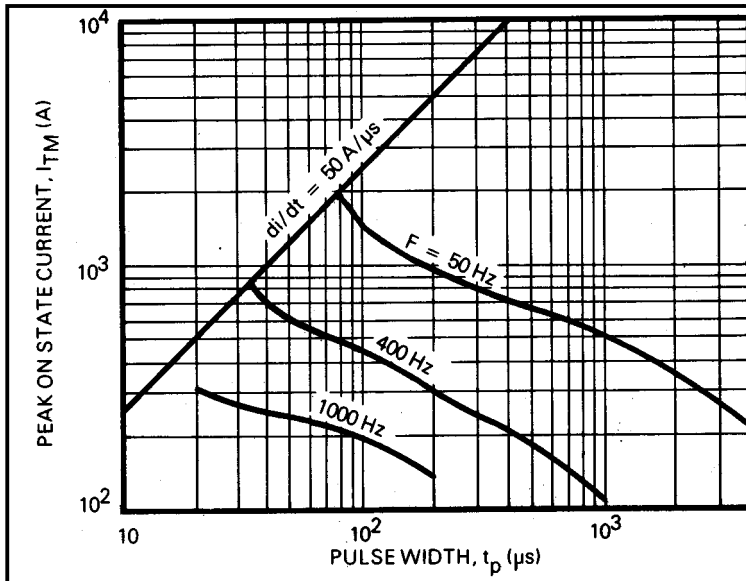


Fig.14 Maximum allowable peak on-state current vs pulse width for $T_{case} = 65^\circ\text{C}$

**NOTES:**

1. $di/dt = 50$ A/ μ s
2. $V_D \leq 600$ V.
3. $V_R \leq 10$ V.
4. R.C Snubber, $C = 0.22$ μ F, $R = 4.7$ Ω

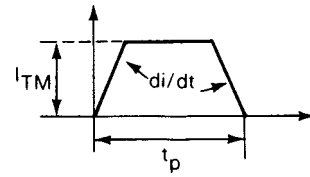
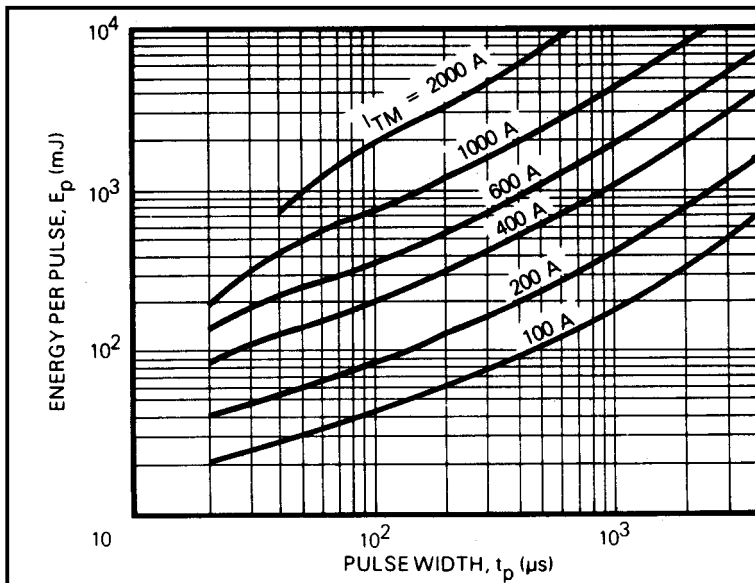


Fig.15 Maximum allowable peak on-state current vs pulse width for $T_{case} = 65^\circ\text{C}$

**NOTES:**

1. $di/dt = 100$ A/ μ s
2. $V_D \leq 600$ V.
3. $V_R \leq 10$ V.
4. R.C Snubber, $C = 0.22$ μ F, $R = 4.7$ Ω

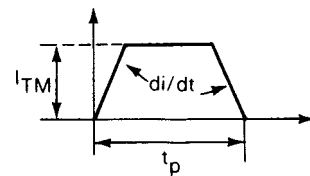
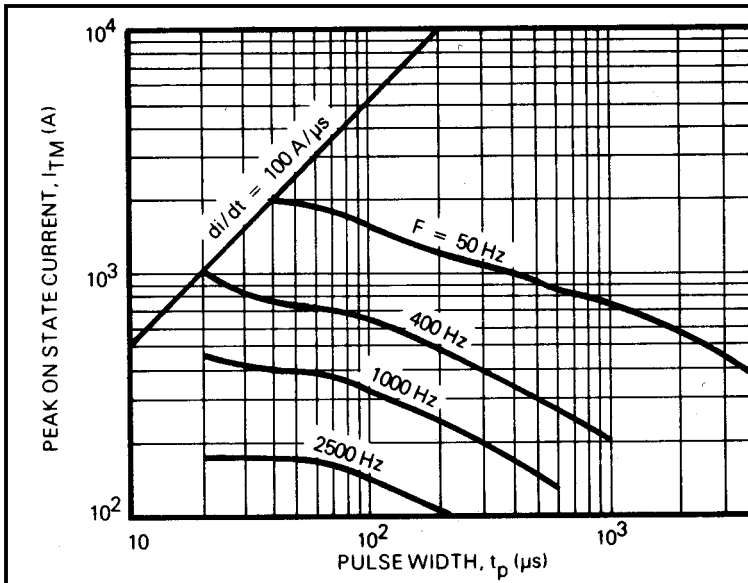


Fig.16 Energy per pulse for trapezoidal pulses



NOTES:

1. $di/dt = 100 \text{ A}/\mu\text{s}$
2. $V_D \leq 600 \text{ V}$.
3. $V_R \leq 10 \text{ V}$.
4. R.C Snubber, $C = 0.22 \mu\text{F}$, $R = 4.7 \Omega$

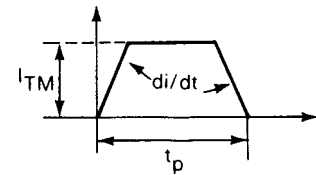
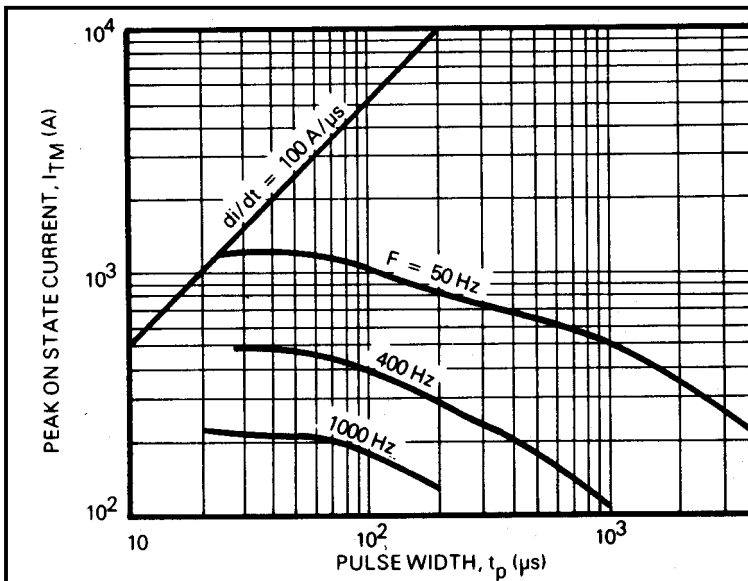


Fig.17 Maximum allowable peak on-state current vs pulse width for $T_{\text{case}} = 65^\circ\text{C}$



NOTES:

1. $di/dt = 100 \text{ A}/\mu\text{s}$
2. $V_D \leq 600 \text{ V}$.
3. $V_R \leq 10 \text{ V}$.
4. R.C Snubber, $C = 0.22 \mu\text{F}$, $R = 4.7 \Omega$

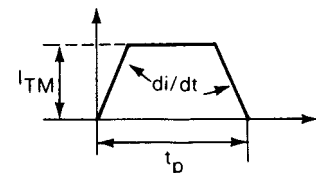
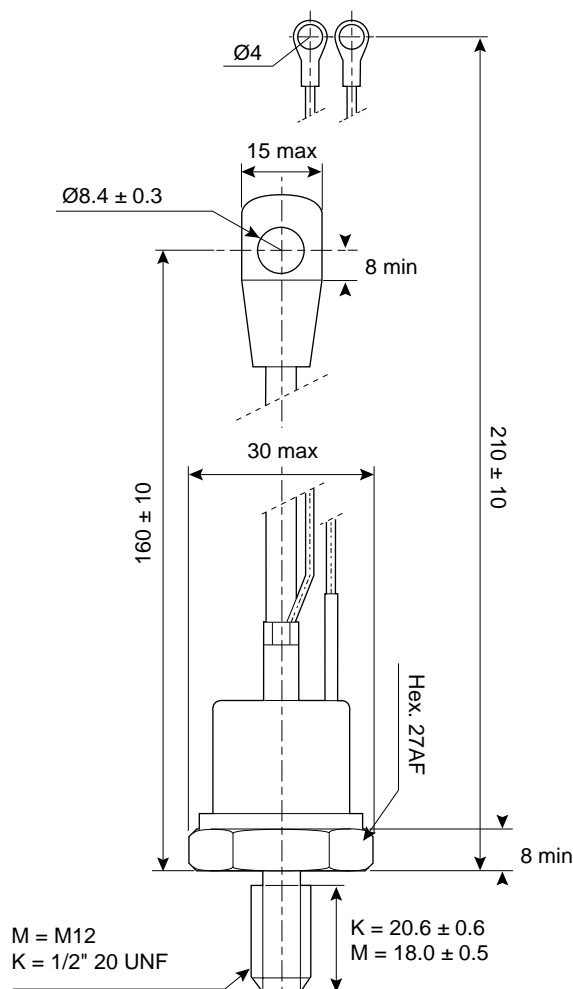


Fig.18 Maximum allowable peak on-state current vs pulse width for $T_{\text{case}} = 90^\circ\text{C}$

PACKAGE DETAILS

For further package information, please contact your nearest Customer Service Centre. All dimensions in mm, unless stated otherwise. DO NOT SCALE.



Nominal weight: 120g
 Mounting torque: 15Nm ±10%
 Gate lead colour: White
 Cathode lead colour: Red

Package outline type code: T094

POWER ASSEMBLY CAPABILITY

The Power Assembly group was set up to provide a support service for those customers requiring more than the basic semiconductor, and has developed a flexible range of heatsink and clamping systems in line with advances in device voltages and current capability of our semiconductors.

We offer an extensive range of air and liquid cooled assemblies covering the full range of circuit designs in general use today. The Assembly group continues to offer high quality engineering support dedicated to designing new units to satisfy the growing needs of our customers.

Using the latest CAD methods our team of design and applications engineers aim to provide the Power Assembly Complete Solution (PACs).

DEVICE CLAMPS

Disc devices require the correct clamping force to ensure their safe operation. The PACS range includes a varied selection of pre-loaded clamps to suit all of our manufactured devices. Types available include cube clamps for single side cooling of 'T' 23mm and 'E' 30mm discs, and bar clamps right up to 83kN for our 'Z' 100mm thyristors and diodes.

Clamps are available for single or double side cooling, with high insulation versions for high voltage assemblies.

Please refer to our application note on device clamping, AN4839

HEATSINKS

The Power Assembly group has its own proprietary range of extruded aluminium heatsinks. They have been designed to optimise the performance of Dynex semiconductors. Data with respect to air natural, forced air and liquid cooling (with flow rates) is available on request.

For further information on device clamps, heatsinks and assemblies, please contact your nearest sales representative or customer service office.



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Target Information: This is the most tentative form of information and represents a very preliminary specification. No actual design work on the product has been started.

Preliminary Information: The product is in design and development. The datasheet represents the product as it is understood but details may change.

Advance Information: The product design is complete and final characterisation for volume production is well in hand.

No Annotation: The product parameters are fixed and the product is available to datasheet specification.

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